

EVOLUTION OF TEMPERATURE DISTRIBUTION  
IN IMPLANTED Si-BASED STRUCTURES: PULSE  
MODE OF LASER IRRADIATION

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S u m m a r y

We present the results explaining the general tendency in peculiarities of the process of heat distribution in semiconductor structures with modified properties of the surface layer under a pulse laser irradiation. It is shown that the presence of a structural inhomogeneity (modified layer) and the influence of a nonlinear dependence of the thermal diffusivity coefficient result in both a substantial transformation of the area of localization (its decrease) of thermal energy and an increase of the surface temperature.